AMENDMENTS TO THE SPECIFICATION:

Please REPLACE the paragraph no. [0019] on page 10 of the Specification with the following amended paragraph:

[0019] In a preferred embodiment, the semiconductor film is substantially made of Si, the catalyst element is a metal element M, and the higher semiconductor compound has a composition of M_xSi_y ~~(x>y)~~ (x < y).

Please REPLACE the paragraph no. [0021] on pages 10 and 11 of the Specification with the following amended paragraph:

[0021] In a preferred embodiment, the semiconductor film is substantially made of Si, the catalyst element is a metal element M, and the lower semiconductor compound has a composition of M_xSi_y ~~(x≤ y)~~ (x ≥ y).

Please REPLACE the paragraph no. [0025] on pages 11 and 12 of the Specification with the following amended paragraph:

[0025] In a preferred embodiment, the crystalline semiconductor layer is substantially made of Si, the catalyst element is a metal element M, and the higher semiconductor compound has a composition of M_xSi_y ~~(x>y)~~ (x < y).

Please REPLACE the paragraph no. [0027] on page 12 of the Specification with the following amended paragraph:

[0027] In a preferred embodiment, the crystalline semiconductor layer is substantially made of Si, the catalyst element is a metal element M, and the lower

semiconductor compound has a composition of M_xSi_y ~~$(x \leq y)$~~ $(x \geq y)$.

Please REPLACE the paragraph no. [0033] on page 13 of the Specification with the following amended paragraph:

[0033] In a preferred embodiment, the crystalline semiconductor layer is substantially made of Si, the catalyst element is a metal element M, and the higher semiconductor compound has a composition of M_xSi_y ~~$(x > y)$~~ $(x < y)$.

Please REPLACE the paragraph no. [0035] on page 13 of the Specification with the following amended paragraph:

[0035] In a preferred embodiment, the crystalline semiconductor layer is substantially made of Si, the catalyst element is a metal element M, and the lower semiconductor compound has a composition of M_xSi_y ~~$(x \leq y)$~~ $(x \geq y)$.

Please REPLACE the paragraph no. [0053] on page 17 of the Specification with the following amended paragraph:

[0053] In a preferred embodiment, the crystalline semiconductor layer is substantially made of Si, the catalyst element is a metal element M, and the higher semiconductor compound has a composition of M_xSi_y ~~$(x > y)$~~ $(x < y)$.

Please REPLACE the paragraph no. [0055] on page 17 of the Specification with the following amended paragraph:

[0055] In a preferred embodiment, the crystalline semiconductor layer is substantially made of Si, the catalyst element is a metal element M, and the lower

semiconductor compound has a composition of M_xSi_y ~~$(x \leq y)$~~ $(x \geq y)$.

Please REPLACE the paragraph nos. [0123] and [0124] on page 38 of the Specification with the following amended paragraphs:

[00123] It is preferred that the step (c) includes a step of removing a higher semiconductor compound of the catalyst element, and the low-catalyst-concentration region includes substantially no higher semiconductor compound. For example, the crystalline semiconductor layer is preferably substantially made of Si, the catalyst element is a metal element M, and the higher semiconductor compound has a composition of M_xSi_y ~~$(x>y)$~~$(x < y)$.

[00124] It is preferred that the step (d) includes a step of moving the catalyst element forming a lower semiconductor compound of the catalyst element, and the low-catalyst-concentration region includes substantially no lower semiconductor compound. For example, the crystalline semiconductor layer is substantially made of Si, the catalyst element is a metal element M, and the lower semiconductor compound has a composition of M_xSi_y ~~$(x \leq y)$~~$(x \geq y)$.